

**Topic Title:** 05. Active-Matrix Devices

**Session Title:** 03. Stability Issues in Oxide TFT

[03\_05\_1737] [Invited]

**Defects, Hydrogen, and Light-Induced Instability Mechanism in Amorphous Oxide Semiconductors**

John Robertson (Cambridge Univ., UK)

[03\_05\_1292]

**Effects of Hydrogen on Amorphous InGaZnO Thin-Film Transistors With Hydrogen Barrier Gate Insulator**

KyoungRok Kim, Wan-ho Choi, Seokgoo Jeong, Hyun-Mo Lee, and Jin-Seong Park (Hanyang Univ., Korea)

[03\_05\_1618]

**The Analysis of Anomalous Threshold Voltage Shifts in Oxide Semiconductor Thin-Film Transistors under Positive Gate Bias Stress**

Chihun Sung (ETRI, Korea and Univ. of Science and Tech., Korea), Hee-Ok Kim (ETRI, Korea), Tae-Youb Kim (ETRI, Korea and Univ. of Science and Tech., Korea), and Sung Haeng Cho (ETRI, Korea)

[03\_05\_1660]

**Effect of IGZO/ZnON Tandem Structure on Improving Bias Stress Stability**

Yoon-Seo Kim, Hyun-Mo Lee, and Jin-Seong Park (Hanyang Univ., Korea)

[03\_05\_1459]

**Low-Temperature Crystallization Process for High-Quality Metal Oxide TFTs**

Jae Cheol Shin (Chung-Ang Univ., Korea), Sung Woon Cho (Suncheon Nat'l Univ., Korea), and Sung Kyu Park (Chung-Ang Univ., Korea)